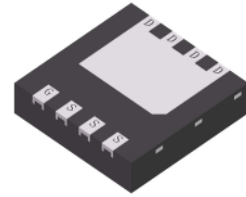


LNB8350DT0AG

N-Channel 30-V (D-S) MOSFET

1. FEATURES

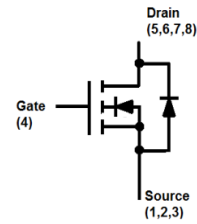
- Low RDS(on) trench technology.
- Low thermal impedance.
- Fast switching speed.
- We declare that the material of product are Halogen Free and compliance with RoHS requirements.



DFN3333-8A

2. APPLICATION

- Power Routing
- DC/DC Conversion
- Motor Drives



3. ORDERING INFORMATION

Device	Marking	Shipping
LNB8350DT0AG	N50	2000/Tape&Reel

4. MAXIMUM RATINGS(Ta = 25°C unless otherwise stated)

Parameter	Symbol	Limits	Unit
Drain-to-Source Voltage	VDSS	30	V
Gate-to-Source Voltage	VGS	±20	V
Continuous Drain Current (Note 1)	ID	TA =25°C	19
		TA =70°C	13.5
Pulsed Drain Current (Note 2)	IDM	68	A
Avalanche Current	IAS	21	A
Avalanche energy (L=0.1mH)	EAS	22.05	mJ
Power Dissipation (Note 1)	PD	TA =25°C	2.5
		TC =25°C	20
Operating Junction Temperature	TJ	-55 ~+150	°C
Storage Temperature Range	Tstg	-55 ~+150	

5. THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Unit
Thermal Resistance,Junction-to-Ambient (Note 1)	RθJA	50	°C/W
Thermal Resistance,Junction-to-Ambient (Note 3)	RθJA	160	
Thermal Resistance,Junction-to-Case	RθJC	6	

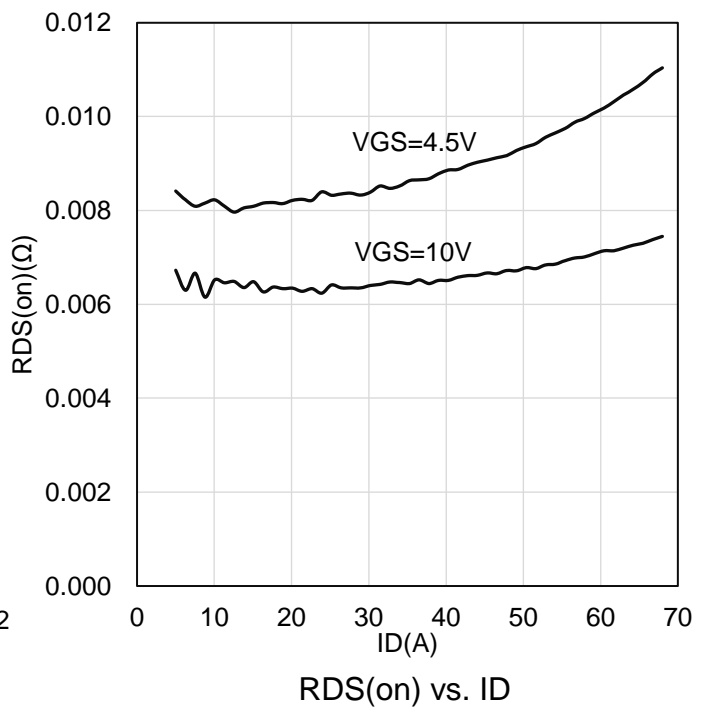
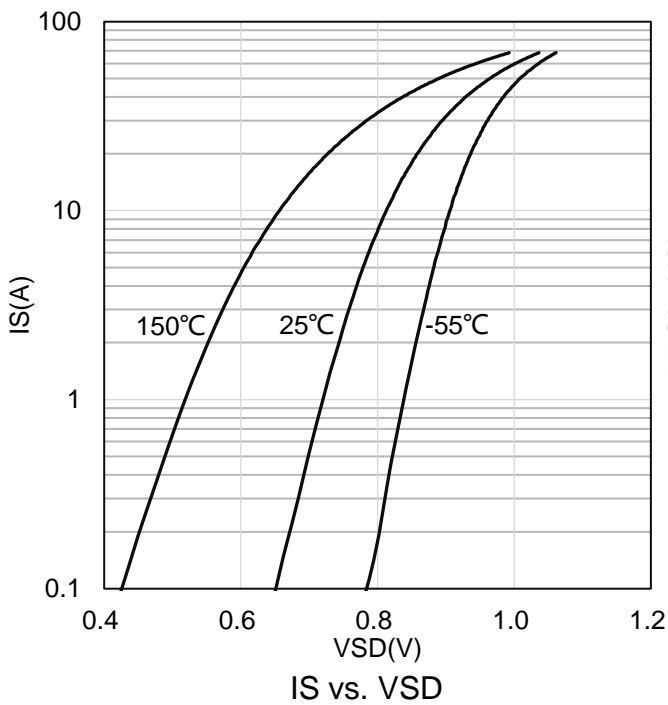
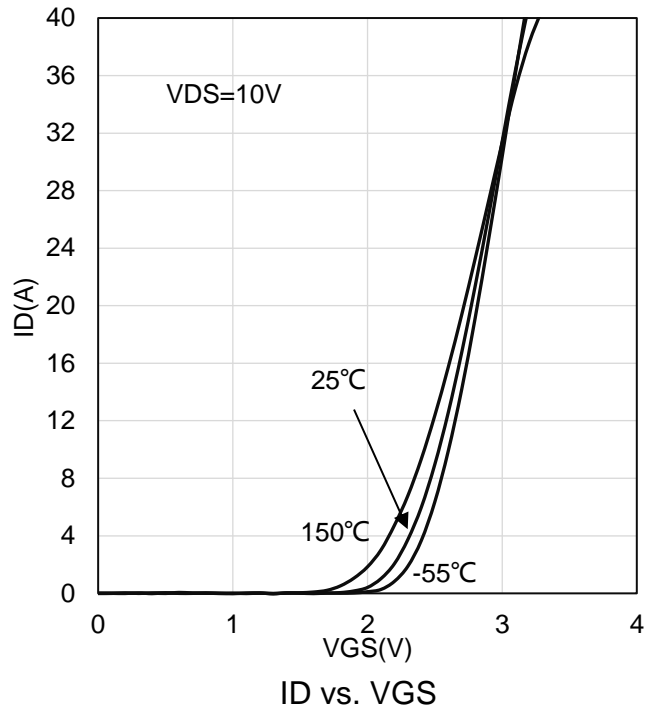
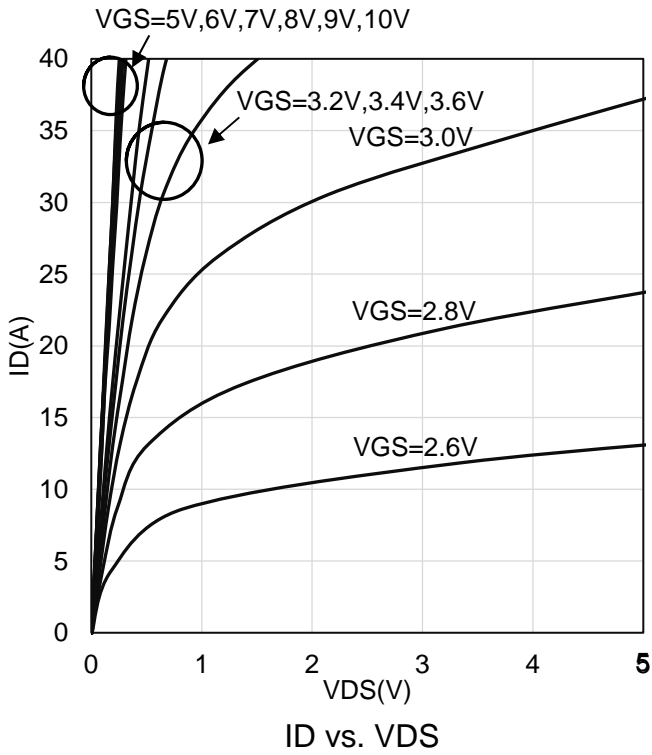
- 1.Surface mounted on 1.5 x 1.5 FR4 board using 1 sq in pad, 2 oz Cu.
- 2.Pulse width limited by maximum junction temperature.
- 3.Surface mounted on FR4 board using the minimum recommended pad size.

6. ELECTRICAL CHARACTERISTICS

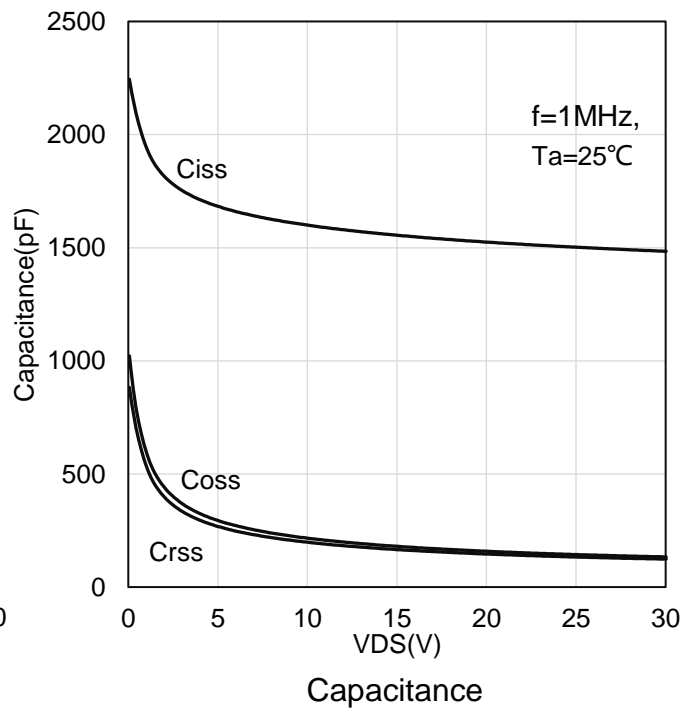
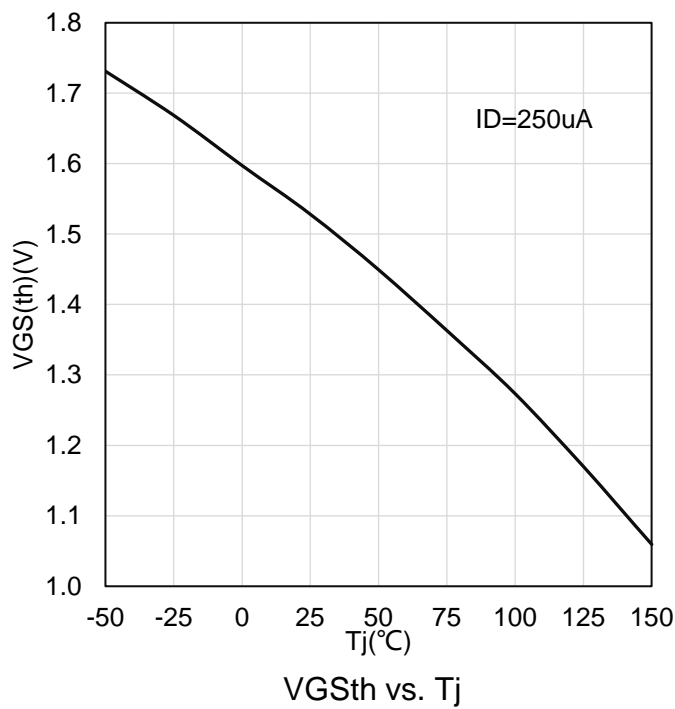
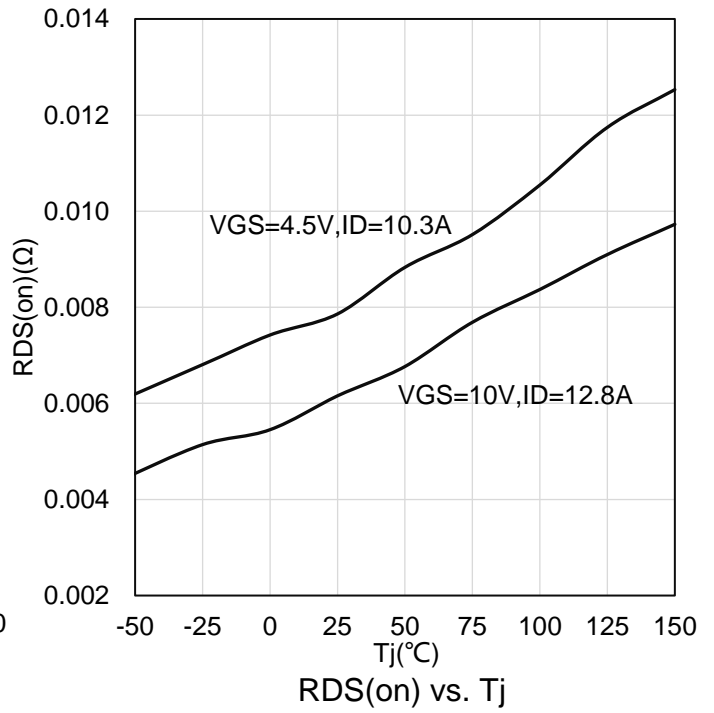
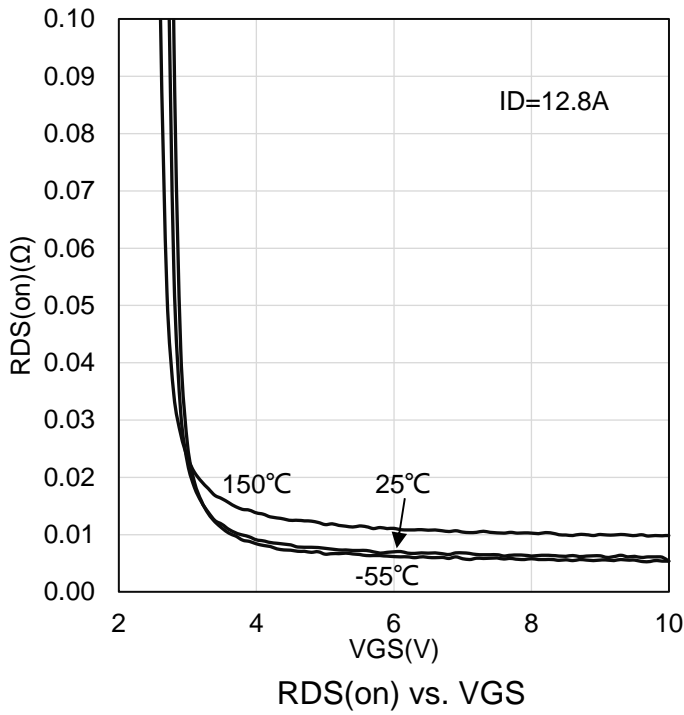
Characteristic	Symbol	Min.	Typ.	Max.	Unit
Static					
Drain-Source Breakdown Voltage (VGS = 0 V, ID = 250 μ A)	V(BR)DSS	30	-	-	V
Gate-Source Threshold Voltage (VDS = VGS, ID = 250 μ A)	VGS(th)	1	1.6	3	V
Gate-Body Leakage (VDS = 0 V, VGS = \pm 20 V)	IGSS	-	-	\pm 1	μ A
Zero Gate Voltage Drain Current (VDS = 24 V, VGS = 0 V) (VDS = 24 V, VGS = 0 V, TJ = 55°C)	IDSS	-	-	1 25	μ A
Drain-Source On-Resistance(Note 4) (VGS = 10 V, ID = 12.8 A) (VGS = 4.5 V, ID = 10.3 A)	RDS(on)	-	6.5 8.5	7.9 10.5	m Ω
Diode Forward Voltage (IS = 2.3 A, VGS = 0 V)	VSD	-	0.78	1.2	V
Dynamic					
Total Gate Charge	(VDS = 15 V, VGS = 4.5 V, ID = 12.8 A)	Qg	-	16	nC
Gate-Source Charge		Qgs	-	5	
Gate-Drain Charge		Qgd	-	5.7	
Input Capacitance	(VDS = 15 V, VGS = 0 V, f = 1 Mhz)	Ciss	-	1578	pF
Output Capacitance		Coss	-	182	
Reverse Transfer Capacitance		Crss	-	165	
Turn-On Delay Time	(VDS = 15 V, RL = 1.2 Ω , ID = 12.8 A, VGEN = 10 V, RGEN = 6 Ω)	td(on)	-	10	ns
Rise Time		tr	-	10	
Turn-Off Delay Time		td(off)	-	48	
Fall Time		tf	-	16	

4. Pulse test: PW \leq 300 μ s duty cycle \leq 2%.

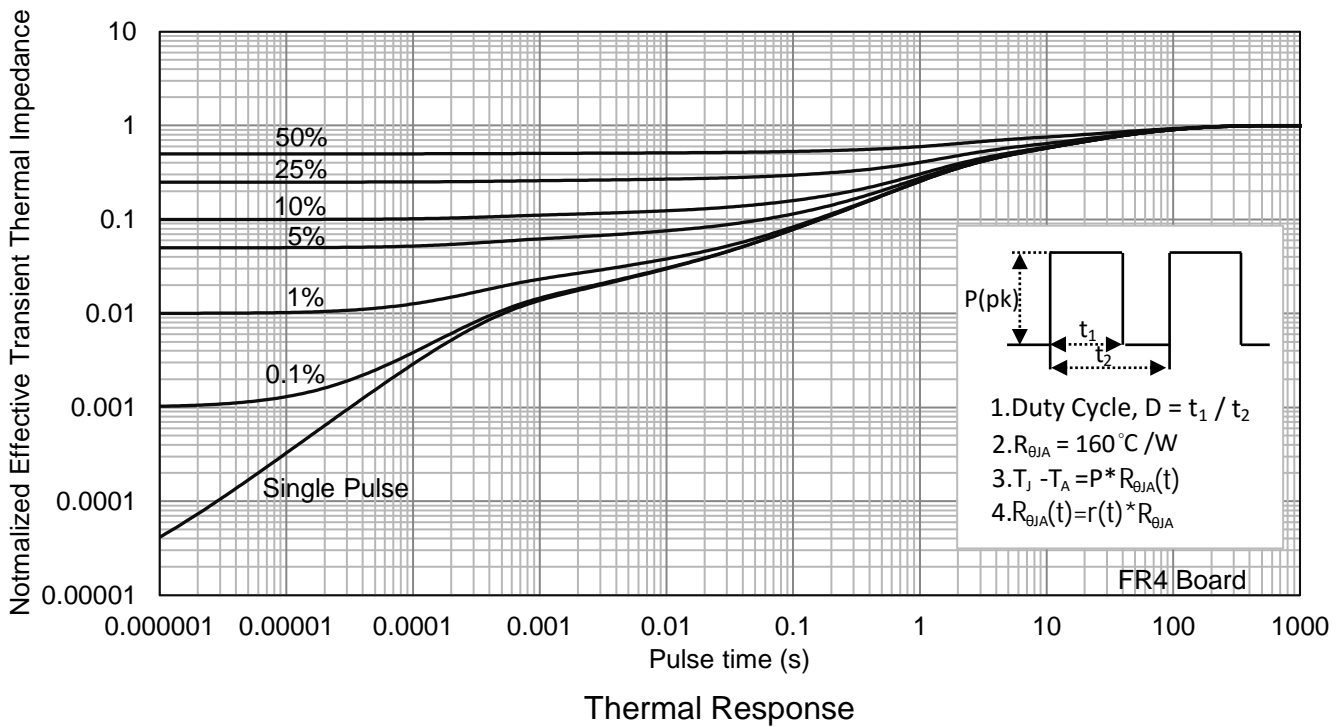
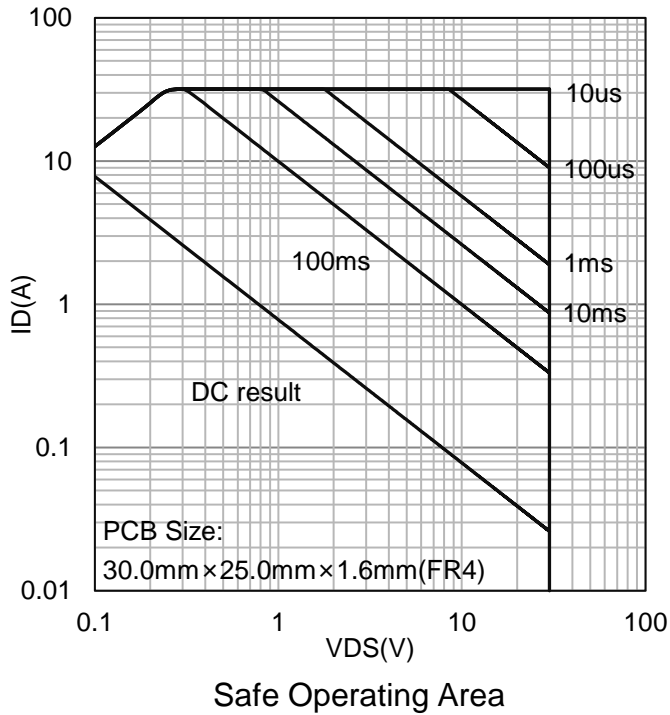
7. ELECTRICAL CHARACTERISTICS CURVES



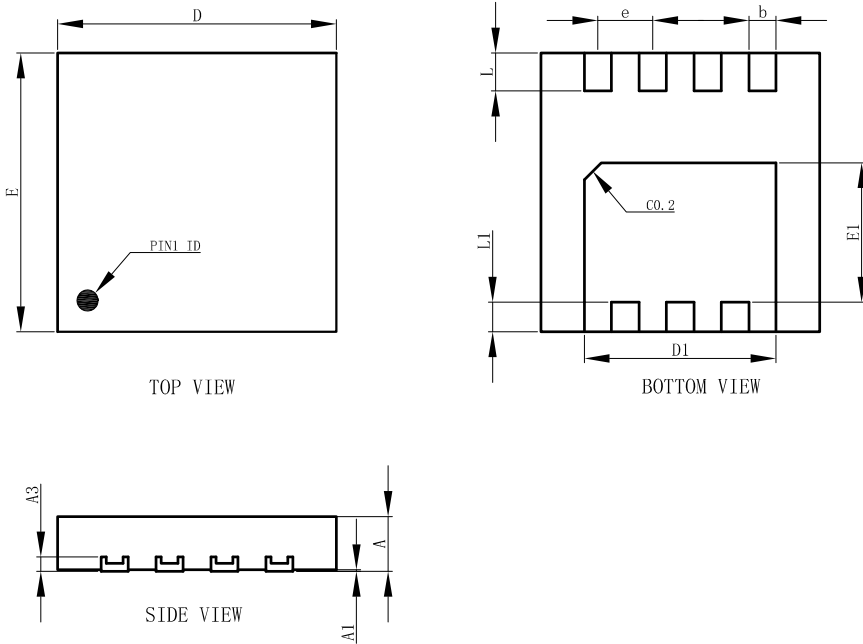
7. ELECTRICAL CHARACTERISTICS CURVES(Con.)



7. ELECTRICAL CHARACTERISTICS CURVES(Con.)

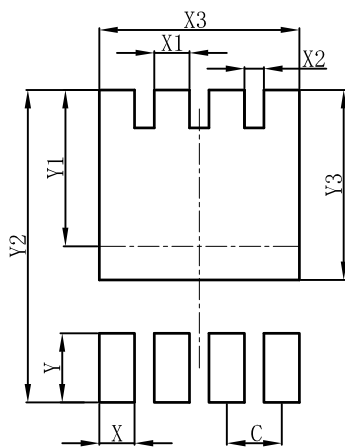


8. OUTLINE AND DIMENSIONS



DFN3333-8A			
DIM	MIN	NOR	MAX
A	0.60	0.65	0.70
A1	0.00	0.03	0.05
b	0.27	0.32	0.37
D	3.25	3.30	3.35
E	3.25	3.30	3.35
D1	2.22	2.27	2.32
E1	1.60	1.65	1.70
e	0.65BSC		
L	0.40	0.45	0.50
L1	0.30	0.35	0.40
A3	0.152REF.		
All Dimensions in mm			

9. SOLDERING FOOTPRINT



DFN3333-8A	
DIM	(mm)
C	0.65
X	0.42
X1	0.42
X2	0.23
X3	2.37
Y	0.70
Y1	1.85
Y2	3.70
Y3	2.25

DISCLAIMER

- Before you use our Products, you are requested to carefully read this document and fully understand its contents. LRC shall not be in any way responsible or liable for failure, malfunction or accident arising from the use of any LRC's Products against warning, caution or note contained in this document.
- All information contained in this document is current as of the issuing date and subject to change without any prior notice. Before purchasing or using LRC's Products, please confirm the latest information with a LRC sales representative.

单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)